Byung Chul Jang

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/3475070/publications.pdf

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20	884	516710 16	794594 19
papers	citations	h-index	g-index

22	22	22	1572
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Conductive-bridging random-access memories for emerging neuromorphic computing. Nanoscale, 2020, 12, 14339-14368.	5.6	46
2	Bioinspired Polydopamineâ€Based Resistiveâ€Switching Memory on Cotton Fabric for Wearable Neuromorphic Device Applications. Advanced Materials Technologies, 2019, 4, 1900151.	5.8	33
3	Largeâ€Scale, Lowâ€Power Nonvolatile Memory Based on Fewâ€Layer MoS₂ and Ultrathin Polymer Dielectrics. Advanced Electronic Materials, 2019, 5, 1800688.	5.1	23
4	Polymer Analog Memristive Synapse with Atomic-Scale Conductive Filament for Flexible Neuromorphic Computing System. Nano Letters, 2019, 19, 839-849.	9.1	139
5	Memristive Logicâ€inâ€Memory Integrated Circuits for Energyâ€Efficient Flexible Electronics. Advanced Functional Materials, 2018, 28, 1704725.	14.9	57
6	A Recoverable Synapse Device Using a Threeâ€Dimensional Silicon Transistor. Advanced Functional Materials, 2018, 28, 1804844.	14.9	34
7	First Demonstration of a Logic-Process Compatible Junctionless Ferroelectric FinFET Synapse for Neuromorphic Applications. IEEE Electron Device Letters, 2018, 39, 1445-1448.	3.9	121
8	Zero-static-power nonvolatile logic-in-memory circuits for flexible electronics. Nano Research, 2017, 10, 2459-2470.	10.4	39
9	Lowâ€Power Nonvolatile Charge Storage Memory Based on MoS₂ and an Ultrathin Polymer Tunneling Dielectric. Advanced Functional Materials, 2017, 27, 1703545.	14.9	43
10	Functional Circuitry on Commercial Fabric via Textile-Compatible Nanoscale Film Coating Process for Fibertronics. Nano Letters, 2017, 17, 6443-6452.	9.1	62
11	Comprehensive Study on the Relation Between Low-Frequency Noise and Asymmetric Parasitic Resistances in a Vertical Pillar-Type FET. IEEE Electron Device Letters, 2017, 38, 1008-1011.	3.9	6
12	A Lowâ€Voltage Organic Complementary Inverter with High Operation Stability and Flexibility Using an Ultrathin iCVD Polymer Dielectric and a Hybrid Encapsulation Layer. Advanced Electronic Materials, 2016, 2, 1500385.	5.1	29
13	Flexible Nonvolatile Polymer Memory Array on Plastic Substrate via Initiated Chemical Vapor Deposition. ACS Applied Materials & Interfaces, 2016, 8, 12951-12958.	8.0	66
14	Multilevel resistive switching nonvolatile memory based on MoS ₂ nanosheet-embedded graphene oxide. 2D Materials, 2016, 3, 034002.	4.4	69
15	Conductive Graphitic Channel in Graphene Oxideâ€Based Memristive Devices. Advanced Functional Materials, 2016, 26, 7406-7414.	14.9	54
16	Floating gate memory based on MoS<inf>2</inf> channel and iCVD polymer tunneling dielectric. , 2016, , .		2
17	Memristive Devices: Conductive Graphitic Channel in Graphene Oxide-Based Memristive Devices (Adv.) Tj ETQq1 1 0.784314 rgBT /Ov	14.9	0
18	Multilayer Graphene with a Rippled Structure as a Spacer for Improving Plasmonic Coupling. Advanced Functional Materials, 2016, 26, 5093-5101.	14.9	33

#	Article	IF	Citations
19	Experimental study on quantum mechanical effect for insensitivity of threshold voltage against temperature variation in strained SOI MOSFETs. , 2015, , .		4
20	Ultra-low power, highly uniform polymer memory by inserted multilayer graphene electrode. 2D Materials, 2015, 2, 044013.	4.4	21